WAFER PROCESSING METHOD AND WAFER PROCESSING APPARATUS

ABSTRACT OF THE DISCLOSURE

A wafer processing method comprising the steps of grinding an underside of a wafer which is provided, on its front surface, with a plurality of semiconductor devices; polishing a ground surface formed by the grinding operation; carrying out a plasma-processing for a polished surface formed by the polishing operation under a predetermined gaseous atmosphere of CF_4 or SF_6 in a plasma chamber, to roughen the polished surface; and forming a metal coating onto the roughened underside of the water and the apparatus for carrying out this method.

(Fig. 1)